

High Voltage MOSFET

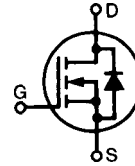
IXTH 1N100
IXTT 1N100

$$V_{DSS} = 1000 \text{ V}$$

$$I_{D25} = 1.5 \text{ A}$$

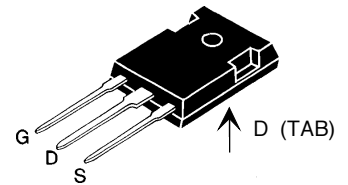
$$R_{DS(on)} = 11 \text{ } \Omega$$

N-Channel Enhancement Mode
Avalanche Energy Rated

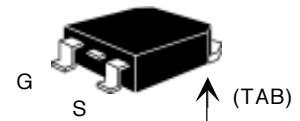


Symbol	Test Conditions	Maximum Ratings	
V_{DSS}	$T_J = 25^\circ\text{C}$ to 150°C	1000	V
V_{DGR}	$T_J = 25^\circ\text{C}$ to 150°C ; $R_{GS} = 1 \text{ M}\Omega$	1000	V
V_{GS}	Continuous	± 20	V
V_{GSM}	Transient	± 30	V
I_{D25}	$T_C = 25^\circ\text{C}$	1.5	A
I_{DM}	$T_C = 25^\circ\text{C}$, pulse width limited by T_{JM}	6	A
I_{AR}		1.5	A
E_{AR}	$T_C = 25^\circ\text{C}$	6	mJ
E_{AS}	$T_C = 25^\circ\text{C}$	200	mJ
dv/dt	$I_S \leq I_{DM}$, $di/dt \leq 100 \text{ A}/\mu\text{s}$, $V_{DD} \leq V_{DSS}$, $T_J \leq 150^\circ\text{C}$, $R_G = 18 \text{ } \Omega$	3	V/ns
P_D	$T_C = 25^\circ\text{C}$	60	W
T_J		-55 ... +150	$^\circ\text{C}$
T_{JM}		150	$^\circ\text{C}$
T_{stg}		-55 ... +150	$^\circ\text{C}$
M_d	Mounting torque (TO-247)	1.13/10	Nm/lb.in.
Weight	TO-268	4	g
	TO-247	6	g
Maximum lead temperature for soldering 1.6 mm (0.062 in.) from case for 10 s		300	$^\circ\text{C}$

TO-247 AD (IXTH)



TO-268 Case Style



G = Gate, D = Drain,
S = Source, TAB = Drain

Features

- International standard packages
- High voltage, Low $R_{DS(on)}$ HDMOS™ process
- Rugged polysilicon gate cell structure
- Fast switching times

Applications

- Switch-mode and resonant-mode power supplies
- Flyback inverters
- DC choppers
- High frequency matching

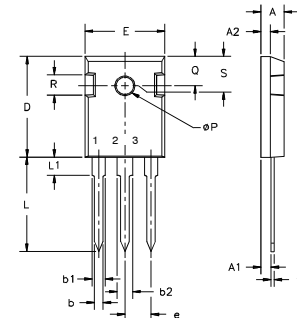
Advantages

- Space savings
- High power density

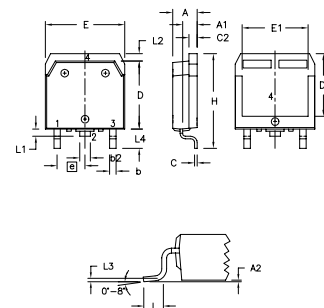
Symbol	Test Conditions	Characteristic Values ($T_J = 25^\circ\text{C}$, unless otherwise specified)		
		min.	typ.	max.
V_{DSS}	$V_{GS} = 0 \text{ V}$, $I_D = 250 \text{ } \mu\text{A}$	1000		V
$V_{GS(th)}$	$V_{DS} = V_{GS}$, $I_D = 25 \text{ } \mu\text{A}$	2.5		4.5 V
I_{GSS}	$V_{GS} = \pm 20 \text{ V}_{DC}$, $V_{DS} = 0$			$\pm 100 \text{ nA}$
I_{DSS}	$V_{DS} = V_{DSS}$ $V_{GS} = 0 \text{ V}$	$T_J = 25^\circ\text{C}$		25 μA
		$T_J = 125^\circ\text{C}$		500 μA
$R_{DS(on)}$	$V_{GS} = 10 \text{ V}$, $I_D = 1.0 \text{ A}$ Pulse test, $t \leq 300 \text{ } \mu\text{s}$, duty cycle $d \leq 2 \%$			11 Ω

Symbol	Test Conditions	Characteristic Values		
		$(T_J = 25^\circ\text{C}, \text{ unless otherwise specified})$		
		min.	typ.	max.
g_{fs}	$V_{DS} = 20\text{ V}; I_D = 1.0\text{ A}, \text{ pulse test}$	0.8	1.5	S
C_{iss}	$V_{GS} = 0\text{ V}, V_{DS} = 25\text{ V}, f = 1\text{ MHz}$		480	pF
C_{oss}			45	pF
C_{rss}			15	pF
$t_{d(on)}$	$V_{GS} = 10\text{ V}, V_{DS} = 0.5 \cdot V_{DSS}, I_D = 1\text{ A}$ $R_G = 18\Omega, \text{ (External)}$		18	ns
t_r			19	ns
$t_{d(off)}$			20	ns
t_f			18	ns
$Q_{g(on)}$	$V_{GS} = 10\text{ V}, V_{DS} = 0.5 \cdot V_{DSS}, I_D = 1\text{ A}$		23	nC
Q_{gs}			4.5	nC
Q_{gd}			14	nC
R_{thJC}	TO-247			2.3 K/W
R_{thCK}			0.25	K/W

Symbol	Test Conditions	Characteristic Values		
		$(T_J = 25^\circ\text{C}, \text{ unless otherwise specified})$		
		min.	typ.	max.
I_S	$V_{GS} = 0\text{ V}$			1.5 A
I_{SM}	Repetitive; pulse width limited by T_{JM}			6 A
V_{SD}	$I_F = I_S, V_{GS} = 0\text{ V},$ Pulse test, $t \leq 300\ \mu\text{s}, \text{ duty cycle } d \leq 2\%$			1.8 V
t_{rr}	$I_F = I_S, -di/dt = 100\text{ A}/\mu\text{s}, V_R = 100\text{ V}$		710	ns

TO-247 AD Outline

 Terminals: 1 - Gate 2 - Drain
 3 - Source Tab - Drain

Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	4.7	5.3	.185	.209
A ₁	2.2	2.54	.087	.102
A ₂	2.2	2.6	.059	.098
b	1.0	1.4	.040	.055
b ₁	1.65	2.13	.065	.084
b ₂	2.87	3.12	.113	.123
C	.4	.8	.016	.031
D	20.80	21.46	.819	.845
E	15.75	16.26	.610	.640
e	5.20	5.72	0.205	0.225
L	19.81	20.32	.780	.800
L1		4.50		.177
ÆP	3.55	3.65	.140	.144
Q	5.89	6.40	0.232	0.252
R	4.32	5.49	.170	.216
S	6.15	BSC	.242	BSC

TO-268 Outline


Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	4.9	5.1	.193	.201
A ₁	2.7	2.9	.106	.114
A ₂	.02	.25	.001	.010
b	1.15	1.45	.045	.057
b ₂	1.9	2.1	.75	.83
C	.4	.65	.016	.026
D	13.80	14.00	.543	.551
E	15.85	16.05	.624	.632
E ₁	13.3	13.6	.524	.535
e	5.45	BSC	.215	BSC
H	18.70	19.10	.736	.752
L	2.40	2.70	.094	.106
L1	1.20	1.40	.047	.055
L2	1.00	1.15	.039	.045
L3		0.25	BSC	.010
L4	3.80	4.10	.150	.161

IXYS reserves the right to change limits, test conditions, and dimensions.



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